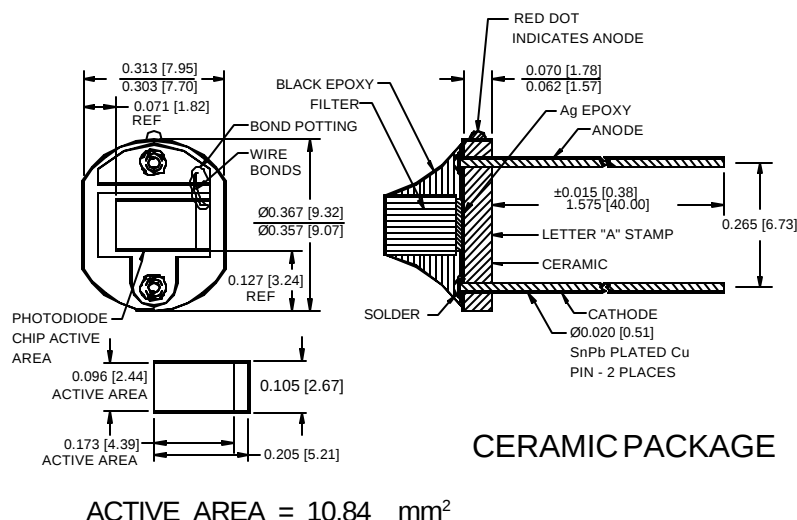


PHOTONIC DETECTORS INC.

Silicon Photodiode, U.V. Enhanced Photovoltaic (center wavelength 360 nm) Type PDU-V401A



PACKAGE DIMENSIONS INCH [mm]



CERAMIC PACKAGE

FEATURES

- Built in filter
- U.V. enhanced
- I.R. blocking

DESCRIPTION

The **PDU-V401A** is a silicon, PIN planar diffused, U.V. enhanced photodiode. Ideal for low noise photovoltaic applications. The filter is a U.V. type A with a center wavelength of 360 nm, with 10⁻³ I.R. blocking. Packaged in a two leaded ceramic base.

APPLICATIONS

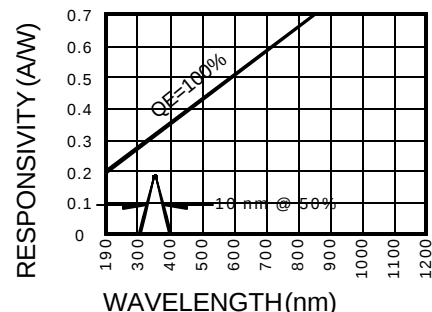
- U.V. detection
- U.V. A sensor
- U.V. radiometer

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		15	V
T _{STG}	Storage Temperature	-55	+100	°C
T _O	Operating Temperature Range	-40	+85	°C
T _S	Soldering Temperature*		+260	°C
I _L	Light Current		0.5	mA

*1/16 inch from case for 3 secs max

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{SC}	Short Circuit Current	H = 100 fc, 2850 K	20	30		μA
I _D	Dark Current	H = 0, V _R = 10 mV		5	10	nA
R _{SH}	Shunt Resistance	H = 0, V _R = 10 mV	100	200		MΩ
TC R _{SH}	RSH Temp. Coefficient	H = 0, V _R = 10 mV		-8		% / °C
C _J	Junction Capacitance	H = 0, V _R = 0 V**		1250		pF
λ _{range}	Spectral Application Range	Spot Scan	300	360	400	nm
R	Responsivity	V _R = 0 V, λ = 360 nm		.10		A/W
V _{BR}	Breakdown Voltage	I = 10 μA	15	30		V
NEP	Noise Equivalent Power	V _R = 2 V @ Peak		1x10 ⁻¹⁴		W/√Hz
tr	Response Time	R _L = 1 KΩ V _R = 0 V		1000		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. **f=1 MHz

[FORM NO. 100-PDU-V401A REV B]